

Vishay Siliconix

Dual P-Channel 30 V (D-S) MOSFET

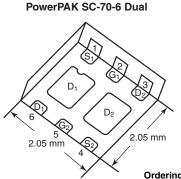
PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)	
- 30	0.087 at V _{GS} = - 10 V	- 4.5 ^a	3.2 nC	
	0.145 at V _{GS} = - 4.5 V	- 4.5 ^a	5.2 110	

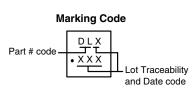
FEATURES

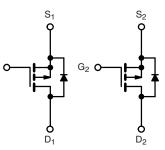
- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK[®] SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

• Power Switch for Motor Drive for Portable Devices







P-Channel MOSFET P-Channel MOSFET

Ordering Information: SiA915DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 30	V	
Gate-Source Voltage		V _{GS}	± 20	v	
	T _C = 25 °C		- 4.5 ^a		
Continuous Drain Current ($T_1 = 150 \ ^{\circ}C$)	T _C = 70 °C		- 4.5 ^a		
Continuous Drain Current (1j = 130 C)	T _A = 25 °C	I _D	- 3.7 ^{b, c}		
	T _A = 70 °C		- 2.9 ^{b, c}	А	
Pulsed Drain Current		I _{DM}	- 15		
Continuous Source-Drain Diode Current	T _C = 25 °C	I _S	- 4.5 ^a		
	T _A = 25 °C	'S	- 1.6 ^{b, c}		
Maximum Power Dissipation	T _C = 25 °C		6.5		
	T _C = 70 °C	P _D	5	w	
	T _A = 25 °C	'D	1.9 ^{b, c}		
	T _A = 70 °C	1	1.2 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) ^{d, e}			260	U	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	52	65	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	12.5	16	0/11	

Notes: a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See solder profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 110 °C/W.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	L 050 A		- 22		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = - 250 μΑ		4.2			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 1.0		- 2.2	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	μΑ	
		$V_{DS} = -30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 ^{\circ}\text{C}$			- 10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 V, V_{GS} = -10 V$	- 10			Α	
Drain Course On Chate Desistence		V _{GS} = - 10 V, I _D = - 2.9 A		0.071	0.087	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 2.2 A		0.118	0.145		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 2.9 A		5		S	
Dynamic ^b							
Input Capacitance	C _{iss}			275		pF	
Output Capacitance	C _{oss}	V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz		60			
Reverse Transfer Capacitance	C _{rss}	-		45			
Takal Qaka Qhanna		V_{DS} = - 15 V, V_{GS} = - 10 V, I_D = - 3.7 A		6	9	nC	
Total Gate Charge	Q _g			3.2	5		
Gate-Source Charge	Q _{gs}	V_{DS} = - 15 V, V_{GS} = - 4.5 V, I_{D} = - 3.7 A		1.1			
Gate-Drain Charge	Q _{gd}	-		1.5			
Gate Resistance	R _g	f = 1 MHz	1.5	7.5	15	Ω	
Turn-On Delay Time	t _{d(on)}			35	70		
Rise Time	t _r	V _{DD} = - 15 V, R _I = 5 Ω		25	50		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -3$ Å, $V_{GEN} = -4.5$ V, $R_g = 1$ Ω		15	30		
Fall Time	t _f	-		10	20		
Turn-On Delay Time	t _{d(on)}			7	15	ns	
Rise Time	t _r	V _{DD} = - 15 V, R _I = 5 Ω		10	20	-	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 3 Å, V_{GEN} = - 10 V, R_g = 1 Ω		15	30		
Fall Time	t _f	-		10	20		
Drain-Source Body Diode Characterist	ics			•			
Continuous Source-Drain Diode Current	ا _S	T _C = 25 °C			- 4.5	٨	
Pulse Diode Forward Current	I _{SM}				- 15	A	
Body Diode Voltage	V _{SD}	$I_{S} = -3 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.87	- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			15	30	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			7	14	nC	
Reverse Recovery Fall Time	t _a	$I_F = -3 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, \text{T}_J = 25 ^\circ\text{C}$		9.5			
Reverse Recovery Rise Time	t _b			5.5		ns	

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

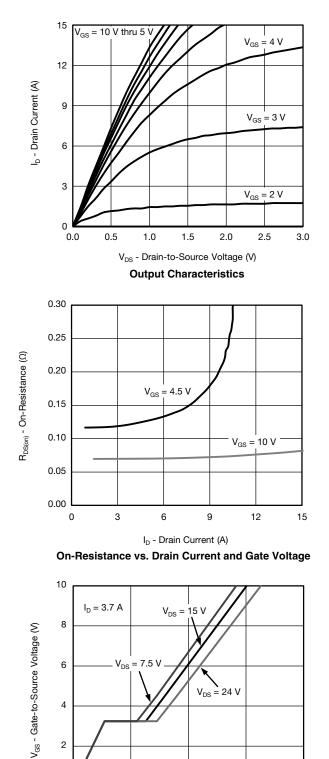
b. Guaranteed by design, not subject to production testing.

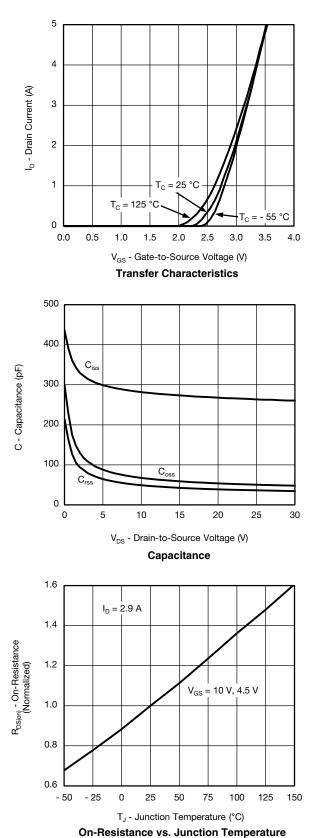
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





0

0

2

4

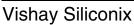
Q_q - Total Gate Charge (nC)

Gate Charge

6

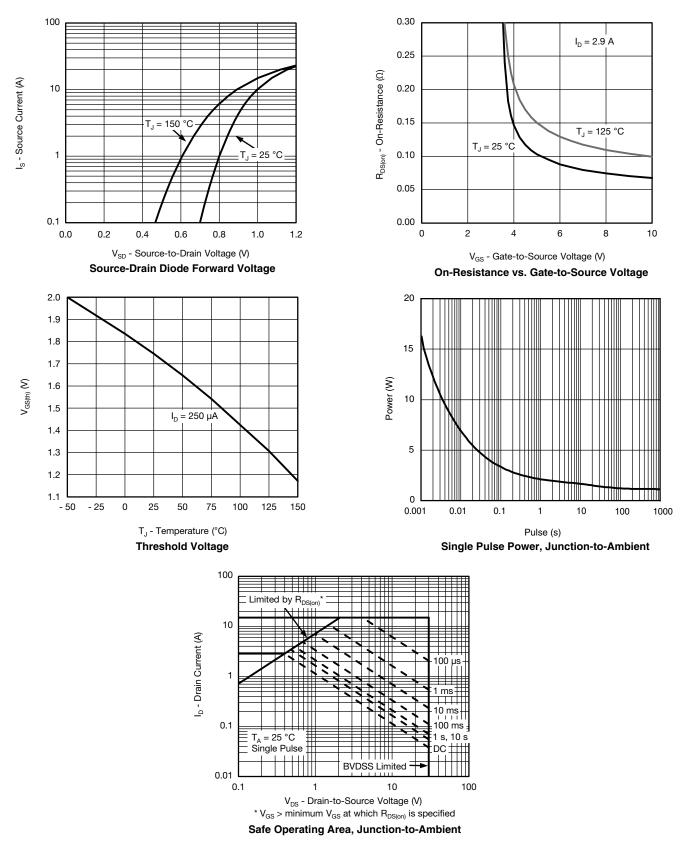
8

SiA915DJ





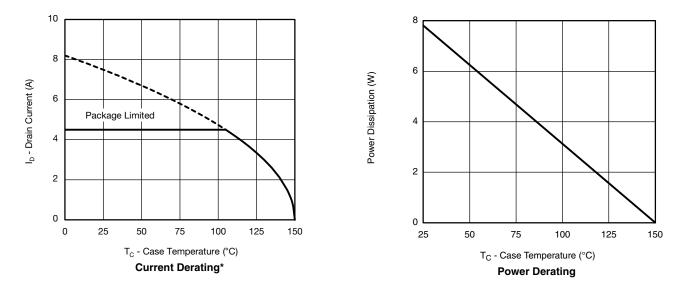
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

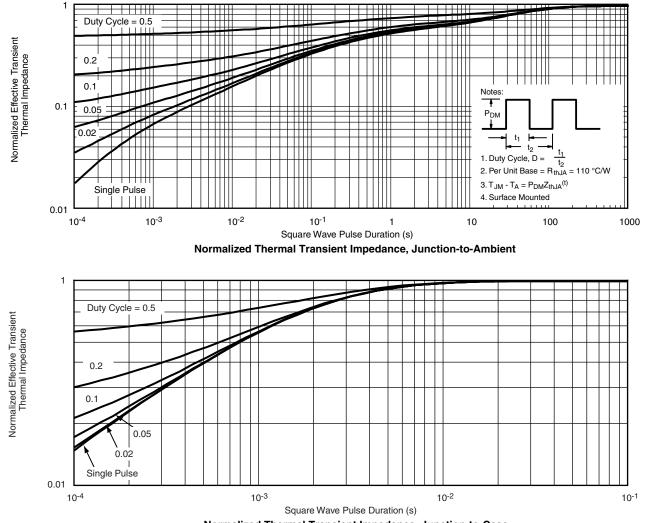


* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67314.



PowerPAK[®] SC70-6L

VISHA

b PIN2 PIN1 PIN3 _ ₹



b

PIN3

__ ₿

PIN2

PIN1

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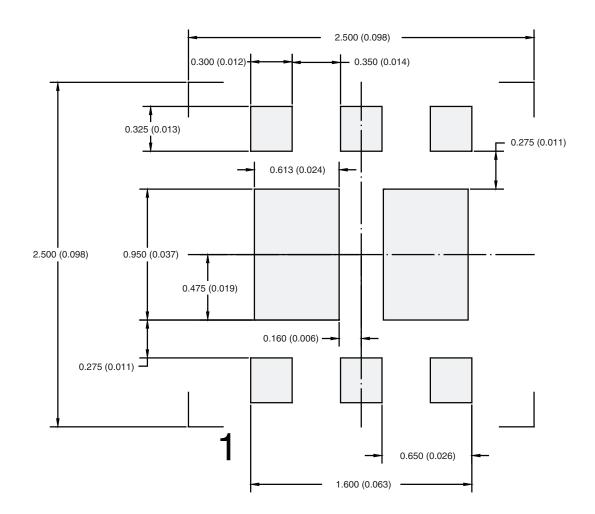
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Application Note 826

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RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm (inches)

Return to Index



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1